



700V 352mΩ N-Ch Power MOSFET

Features

- Extremely Low Gate Charge
- Excellent Output Capacitance (C_{oss}) Profile
- Fast Switching Capability
- 100% UIS Tested, 100% Rg Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

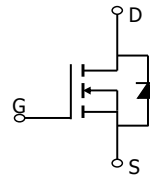
Product Summary

Parameter	Value	Unit
V_{DS}	700	V
$V_{GS(th)}_{Typ}$	3.5	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	12	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$)	352	mΩ
$E_{oss@400V}$	3.6	μJ

Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar
- Lighting / Charger / Adapter

TO-252-3L Top View

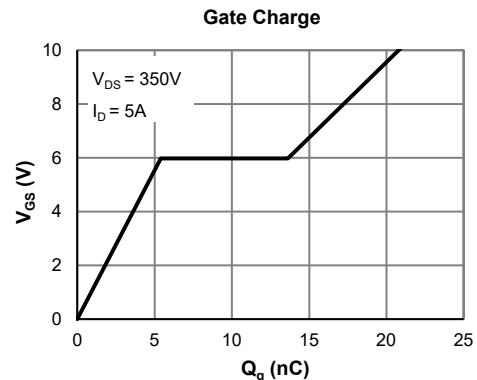
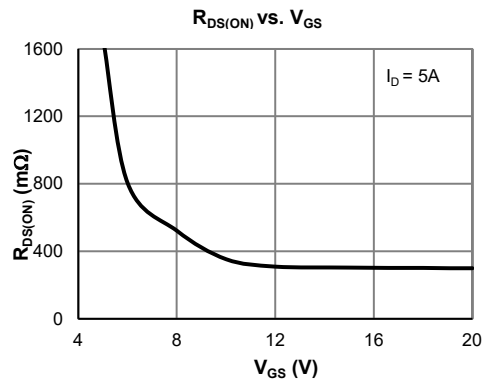


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMH70R430AK-13	TO-252-3L	3	H70R430A	1	-55 to 150	13-inch Reel	2500

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	700	V
Gate-to-Source Voltage	V_{GS}	±30	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	12.0
		$T_C = 100^\circ C$	7.0
Pulsed Drain Current ⁽²⁾	I_{DM}	38	A
Avalanche Energy ⁽³⁾	E_{AS}	180	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	181
		$T_C = 100^\circ C$	72
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C





Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	700			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 560\text{V}, V_{GS} = 0\text{V}$			1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 30\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.5	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 5.5\text{A}$		352	422.0	$\text{m}\Omega$
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			12	A

DYNAMIC PARAMETERS ⁽⁵⁾

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 350\text{V}, f = 1\text{MHz}$		810		pF
Output Capacitance	C_{oss}			27		pF
Reverse Transfer Capacitance	C_{rss}			5.1		pF
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}, V_{DS} = 0 \text{ to } 400\text{V}$		45		pF
Effective output capacitance, time related	$C_{o(tr)}$			190		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		8.8		Ω

SWITCHING PARAMETERS ⁽⁵⁾

Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 700\text{V}, I_D = 5\text{A}$		21		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			13.8		nC
Gate Source Charge	Q_{gs}			5.4		nC
Gate Drain Charge	Q_{gd}			8.2		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 350\text{V}$ $R_L = 75\Omega, R_{GEN} = 6.0\Omega$		13.4		ns
Turn-On Rise Time	t_r			19.4		ns
Turn-Off DelayTime	$t_{D(off)}$			46		ns
Turn-Off Fall Time	t_f			18.6		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		322	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		4560		nC
Peak Diode Recovery Voltage Slope	dv/dt	$I_F \leq 10\text{A}, di/dt = 200\text{A}/\mu\text{s}, V_{DS} = 400\text{V}$		15		V/ns
MOSFET dv/dt Ruggedness	dv/dt	$V_{DS} = 0 \dots 400\text{V}$		50		V/ns

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	28	32	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.69	0.79	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 180 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 10\text{mH}$, $I_{AS} = 6.3\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 350\text{V}$; 100% test at $L = 10\text{mH}$, $I_{AS} = 6.3\text{A}$, $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.



Typical Electrical & Thermal Characteristics

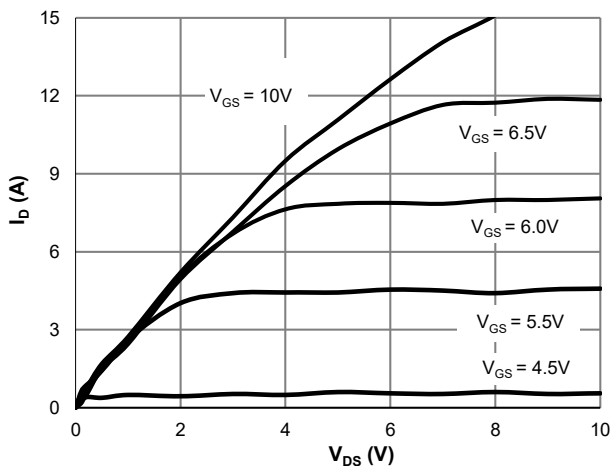


Figure 1: Saturation Characteristics

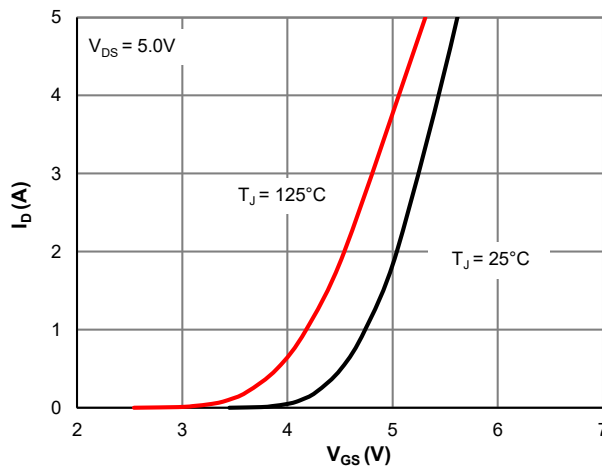


Figure 2: Transfer Characteristics

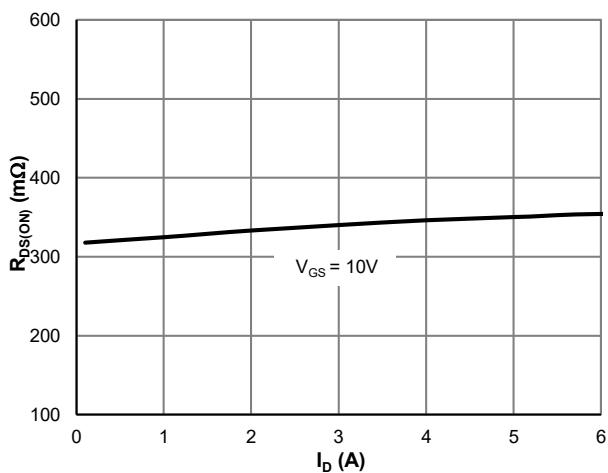


Figure 3: $R_{DS(ON)}$ vs. Drain Current

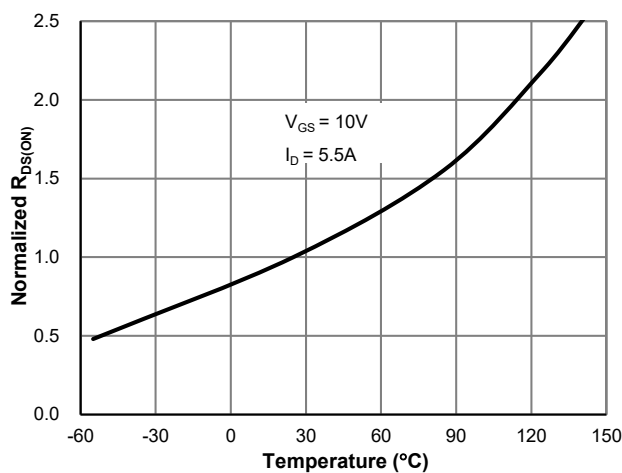


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

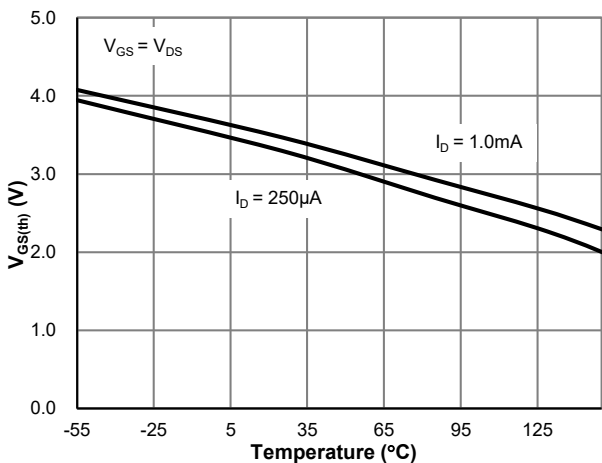


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

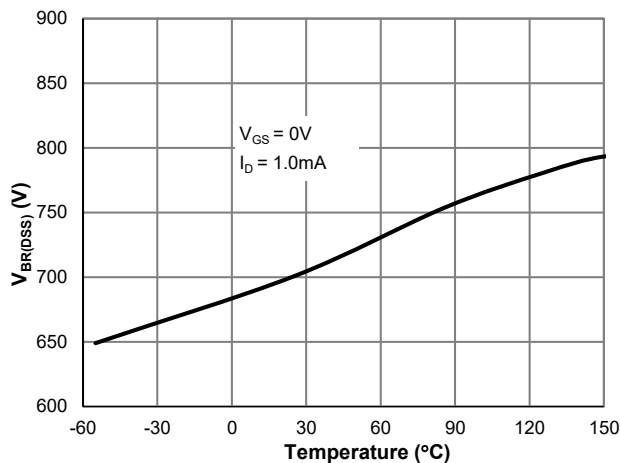
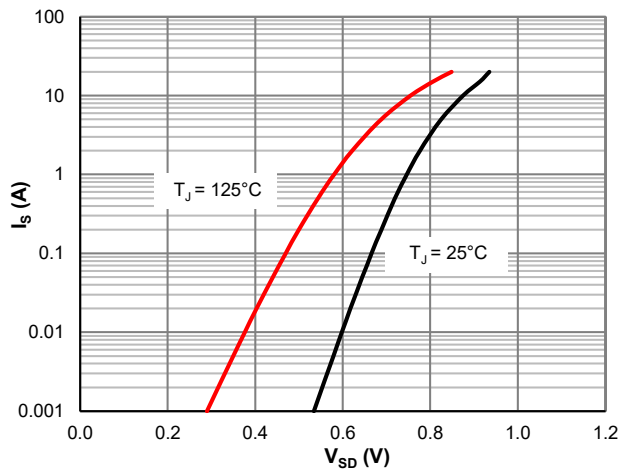
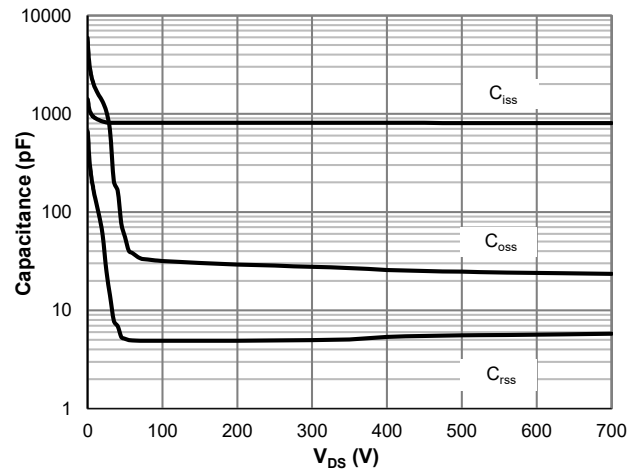
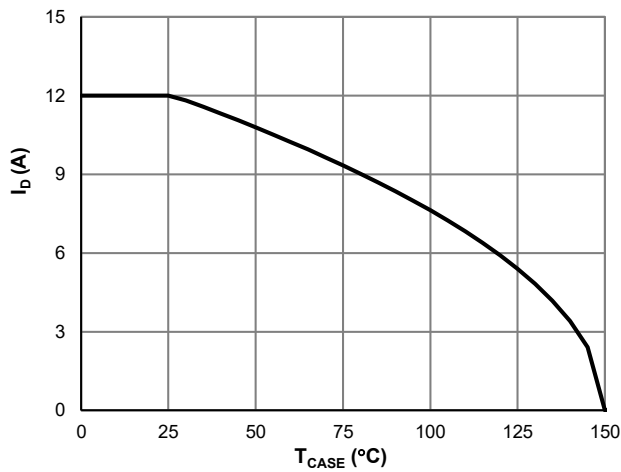
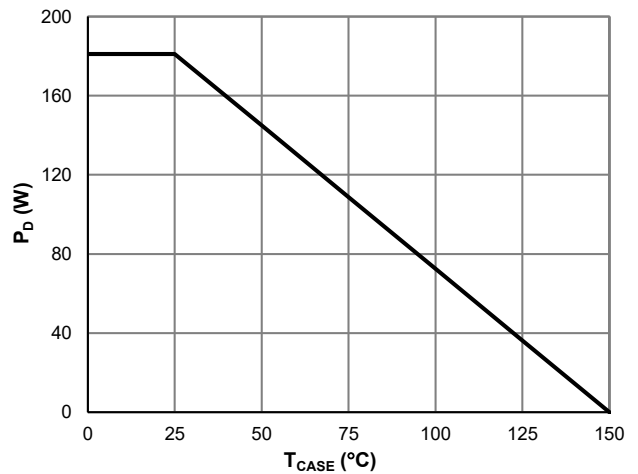
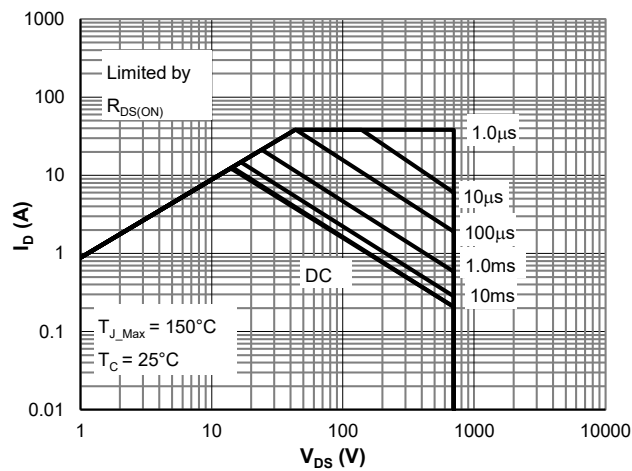
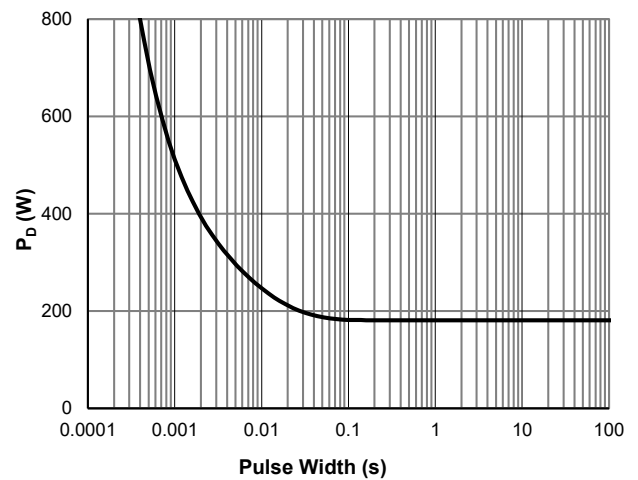


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

Figure 7: Body-Diode Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Current De-rating

Figure 10: Power De-rating

Figure 11: Maximum Safe Operating Area

Figure 12: Single Pulse Power Rating, Junction-to-Case



Typical Electrical & Thermal Characteristics

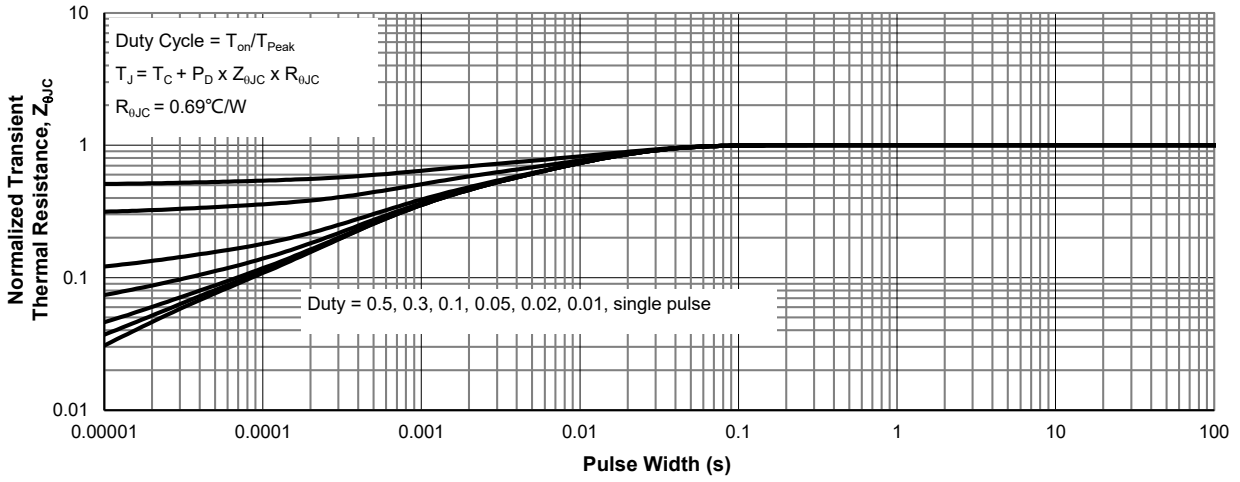
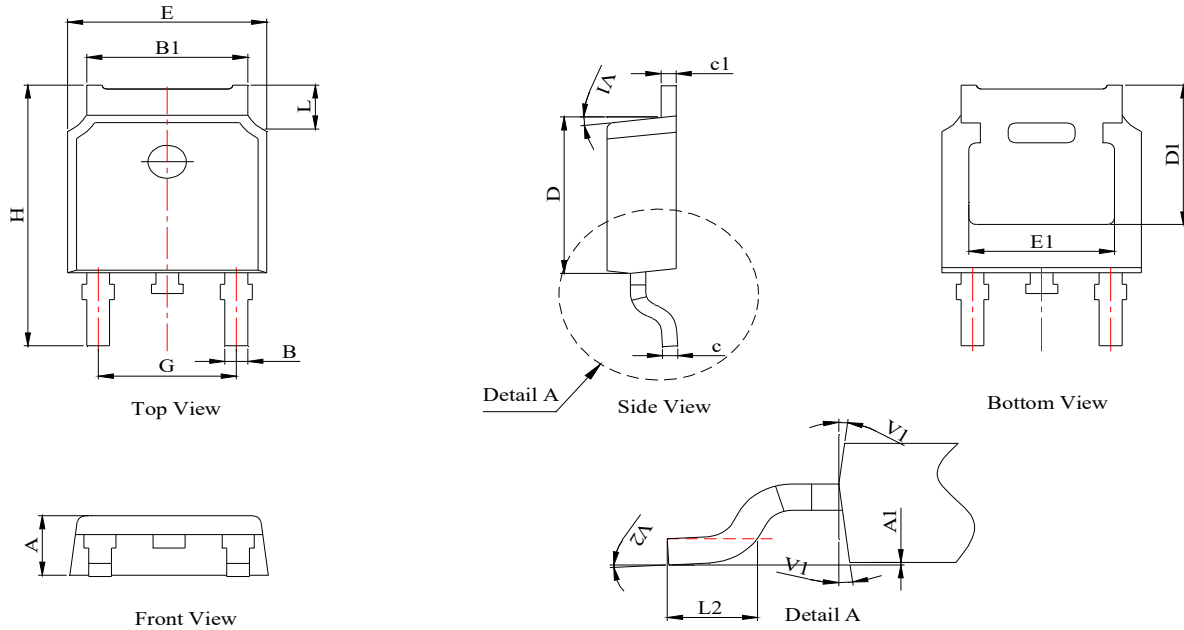
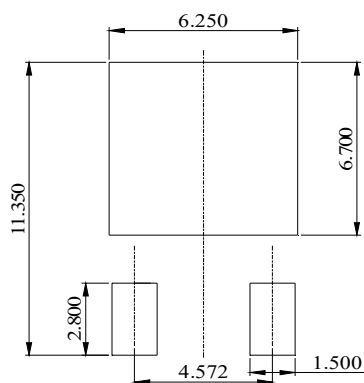


Figure 13: Normalized Maximum Transient Thermal Impedance

TO-252-3L Package Information
Package Outline


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10		2.50
A1	0	-	0.10
B	0.66		0.86
B1	5.18		5.48
c	0.40		0.60
c1	0.44		0.58
D	5.90		6.30
D1	5.30REF		
E	6.40		6.80
E1	4.63		
G	4.47		4.67
H	9.50		10.70
L	1.09		1.21
L2	1.35		1.65
V1		7°	
V2	0°	-	6°

Recommend Soldering Footprint


DIMENSIONS: MILLIMETERS